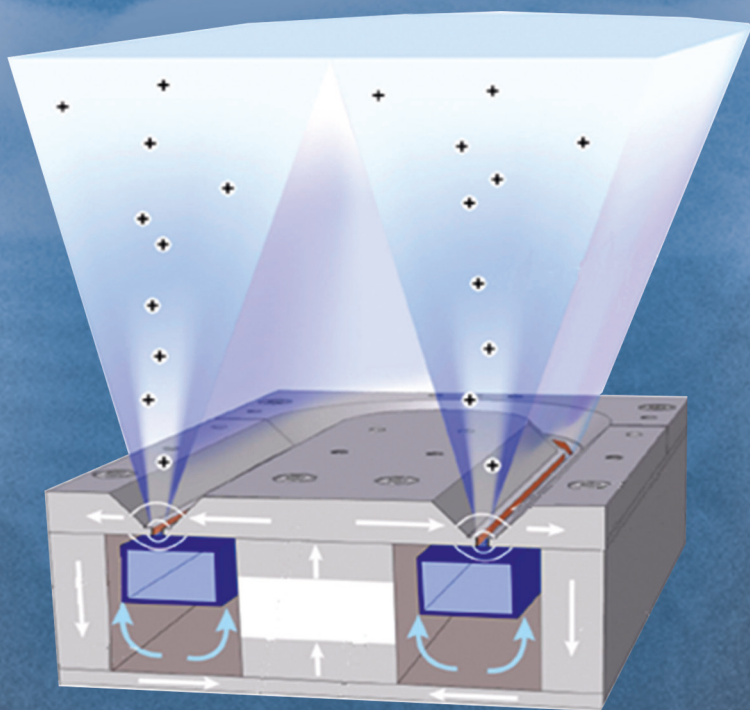




## **Ion Beam Treatment of Functional Layers in Thin-Film Silicon Solar Cells**

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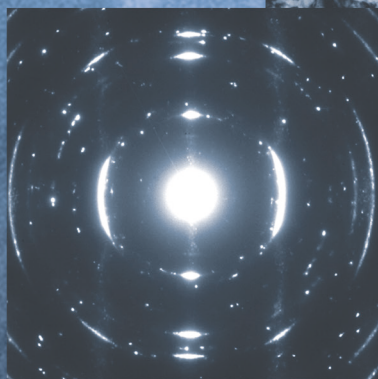
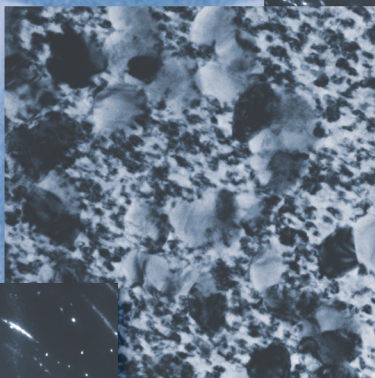
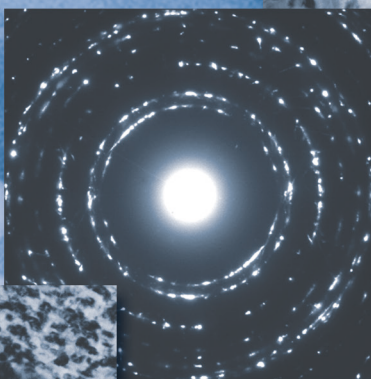
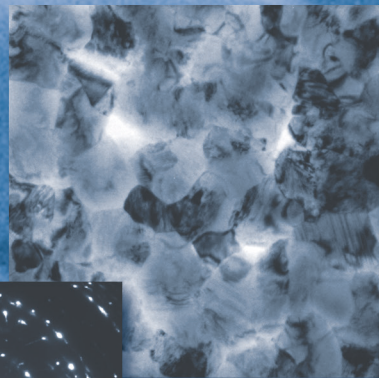
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